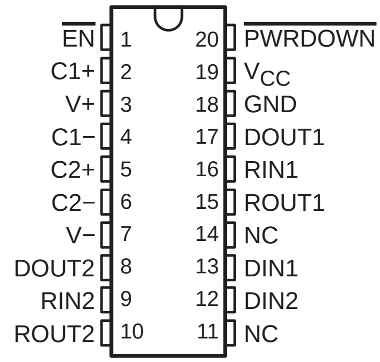
- **RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)**
- **Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operates With 3-V to 5.5-V V_{CC} Supply**
- **Operates Up To 250 kbit/s**
- **Two Drivers and Two Receivers**
- **Low Standby Current . . . 1 µA Typical**
- **External Capacitors . . . 4 × 0.1 µF**
- **Accepts 5-V Logic Input With 3.3-V Supply**
- **Alternative High-Speed Pin-Compatible Device (1 Mbit/s)**
  - **SNx5C3222**
- **Applications**
  - **Battery-Powered Systems, PDAs, Notebooks, Laptops, Palmtop PCs, and Hand-Held Equipment**

DB, DW, OR PW PACKAGE
(TOP VIEW)



NC − No internal connection

description/ordering information

The MAX3222 consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at data signaling rates up to 250 kbit/s and a maximum of 30-V/µs driver output slew rate.

ORDERING INFORMATION

T_A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
−0°C to 70°C	SOIC (DW)	Tube of 25	MAX3222CDW	MAX3222C
		Reel of 2000	MAX3222CDWR	
	SSOP (DB)	Tube of 70	MAX3222CDB	MA3222C
		Reel of 2000	MAX3222CDBR	
	TSSOP (PW)	Tube of 70	MAX3222CPW	MA3222C
		Reel of 2000	MAX3222CPWR	
−40°C to 85°C	SOIC (DW)	Tube of 25	MAX3222IDW	MAX3222I
		Reel of 2000	MAX3222IDWR	
	SSOP (DB)	Tube of 70	MAX3222IDB	MB3222I
		Reel of 2000	MAX3222IDBR	
	TSSOP (PW)	Tube of 70	MAX3222IPW	MB3222I
		Reel of 2000	MAX3222IPWR	

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

description/ordering information (continued)

The MAX3222 can be placed in the power-down mode by setting $\overline{\text{PWRDOWN}}$ low, which draws only 1 µA from the power supply. When the device is powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC}, and V− is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting $\overline{\text{EN}}$ high.

Function Tables

EACH DRIVER

INPUTS		OUTPUT
DIN	$\overline{\text{PWRDOWN}}$	DOUT
X	L	Z
L	H	H
H	H	L

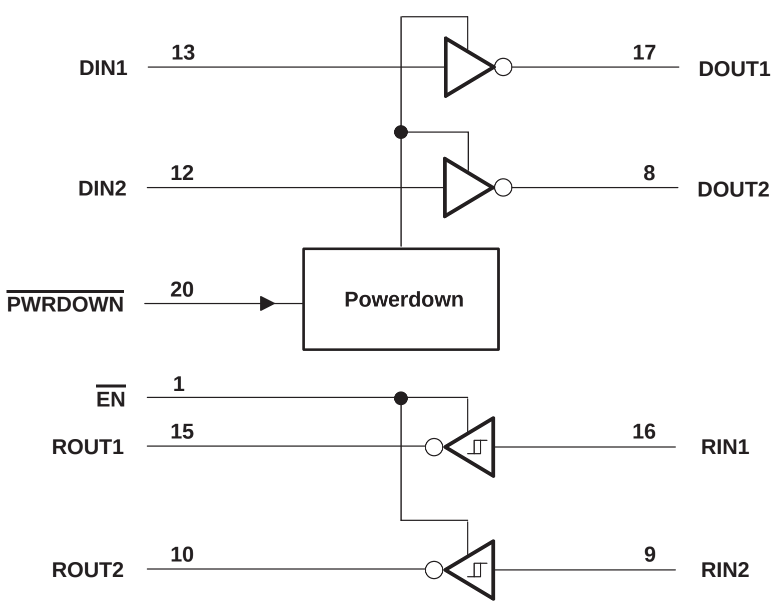
H = high level, L = low level, X = irrelevant, Z = high impedance

EACH RECEIVER

INPUTS		OUTPUT
RIN	$\overline{\text{EN}}$	ROUT
L	L	H
H	L	L
X	H	Z
Open	L	H

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} (see Note 1)		−0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)		−0.3 V to 7 V
Negative output supply voltage range, V− (see Note 1)		0.3 V to −7 V
Supply voltage difference, V+ − V− (see Note 1)		13 V
Input voltage range, V_I:	Drivers, $\overline{EN}$, $\overline{PWRDOWN}$	−0.3 V to 6 V
	Receivers	−25 V to 25 V
Output voltage range, V_O:	Drivers	−13.2 V to 13.2 V
	Receivers	−0.3 V to V_{CC} + 0.3 V
Package thermal impedance, θ_{JA} (see Notes 2 and 3):	DB package	70°C/W
	DW package	58°C/W
	PW package	83°C/W
Operating virtual junction temperature, T_J		150°C
Storage temperature range, T_{stg}		−65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.
2. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) − T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 4 and Figure 5)

				MIN	NOM	MAX	UNIT
	Supply voltage	V_{CC} = 3.3 V		3	3.3	3.6	V
		V_{CC} = 5 V		4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{EN}$, $\overline{PWRDOWN}$		0		5.5	V
V_I	Receiver input voltage			−25		25	V
T_A	Operating free-air temperature	MAX3222C		0		70	°C
		MAX3222I		−40		85	

NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT
I_I	Input leakage current ($\overline{EN}$, $\overline{PWRDOWN}$)			±0.01	±1	µA
I_{CC}	Supply current	No load, $\overline{PWRDOWN}$ at V_{CC}		0.3	1	mA
	Supply current (powered off)	No load, $\overline{PWRDOWN}$ at GND		1	10	µA

‡ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

DRIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	−5	−5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	µA
I_{OS}	Short-circuit output current‡	V_{CC} = 3.6 V,	V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V				
r_o	Output resistance	V_{CC}, V+, and V− = 0 V,	V_O = ±2 V	300	10M		Ω
I_{off}	Output leakage current	$\overline{PWRDOWN}$ = GND, V_{CC} = 3 V to 3.6 V	V_O = ±12 V,			±25	µA
		$\overline{PWRDOWN}$ = GND, V_{CC} = 4.5 V to 5.5 V	V_O = ±10 V,			±25	

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
‡ Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
	Maximum data rate	C_L = 1000 pF, One DOUT switching,	R_L = 3 kΩ, See Figure 1	150	250		kbit/s
$t_{sk(p)}$	Pulse skew§	C_L = 150 pF to 2500 pF, See Figure 2	R_L = 3 kΩ to 7 kΩ,		300		ns
SR(tr)	Slew rate, transition region (See Figure 1)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	6		30	V/µs
			C_L = 150 pF to 2500 pF	4		30	

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
§ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2−C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

RECEIVER SECTION

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = −1 mA	V_{CC} − 0.6 V	V_{CC} − 0.1 V		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis (V_{IT+} − V_{IT-})			0.3		V
I_{off}	Output leakage current	$\overline{EN}$ = V_{CC}		±0.05	±10	μA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

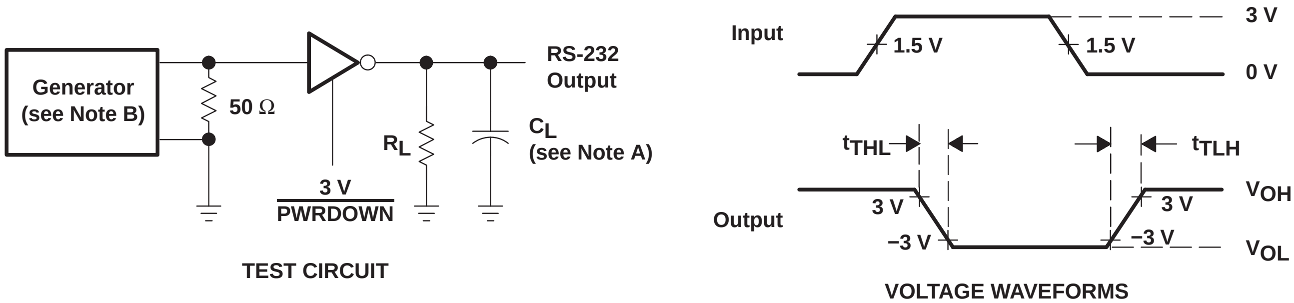
† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2−C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See Figure 3		300		ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L= 150 pF, See Figure 3		300		ns
t_{en}	Output enable time	C_L= 150 pF, R_L = 3 kΩ, See Figure 4		200		ns
t_{dis}	Output disable time	C_L= 150 pF, R_L = 3 kΩ, See Figure 4		200		ns
$t_{sk(p)}$	Pulse skew‡	See Figure 3		300		ns

† All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
‡ Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.
NOTE 4: Test conditions are C1−C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2−C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

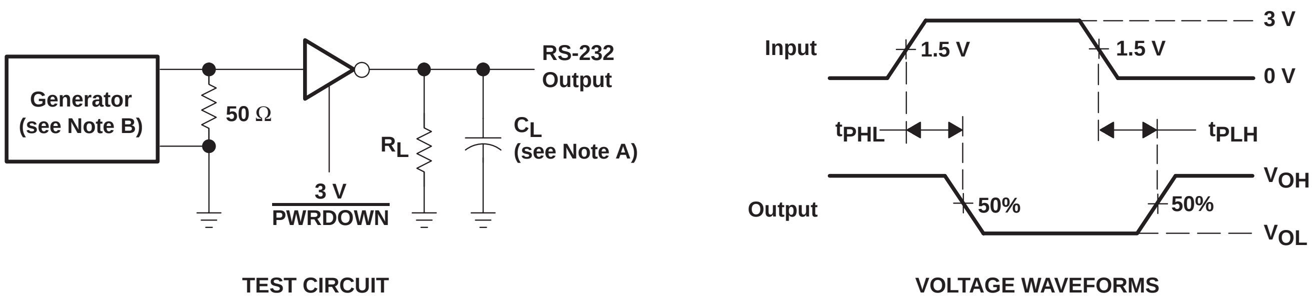
PARAMETER MEASUREMENT INFORMATION



$$SR(tr) = \frac{6\ V}{t_{THL}\ \text{or}\ t_{TLH}}$$

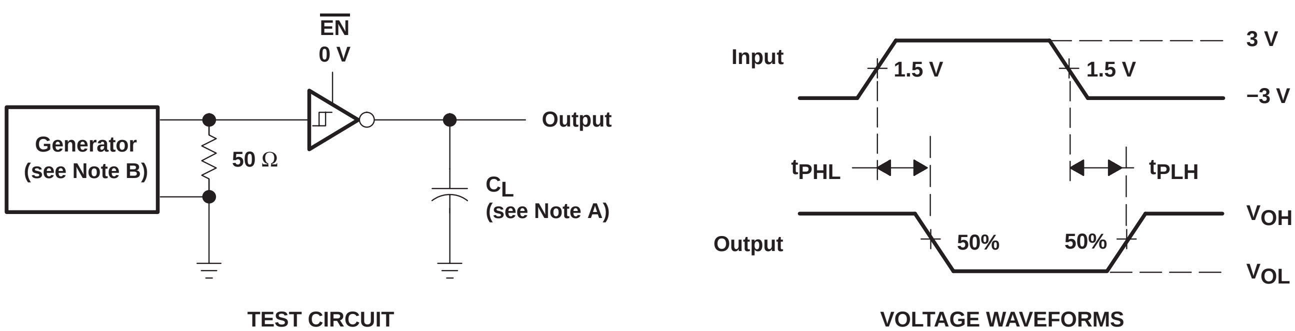
NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

Figure 1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

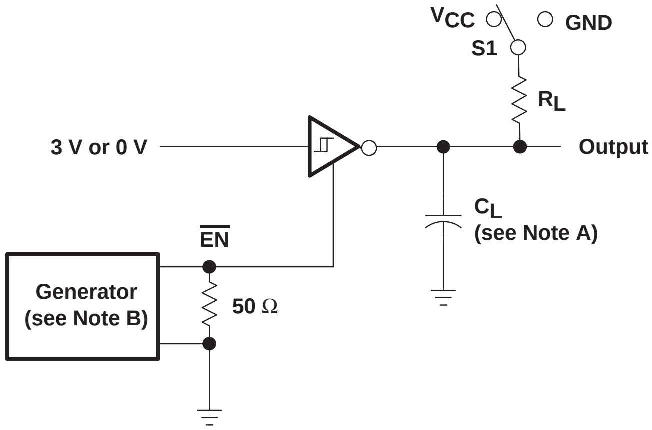
Figure 2. Driver Pulse Skew



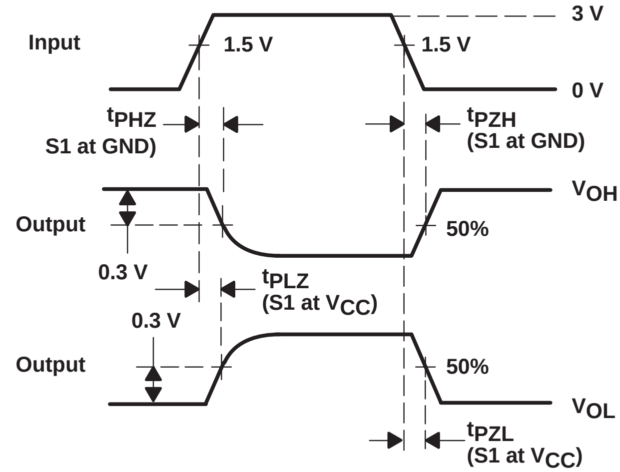
NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

Figure 3. Receiver Propagation Delay Times

PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

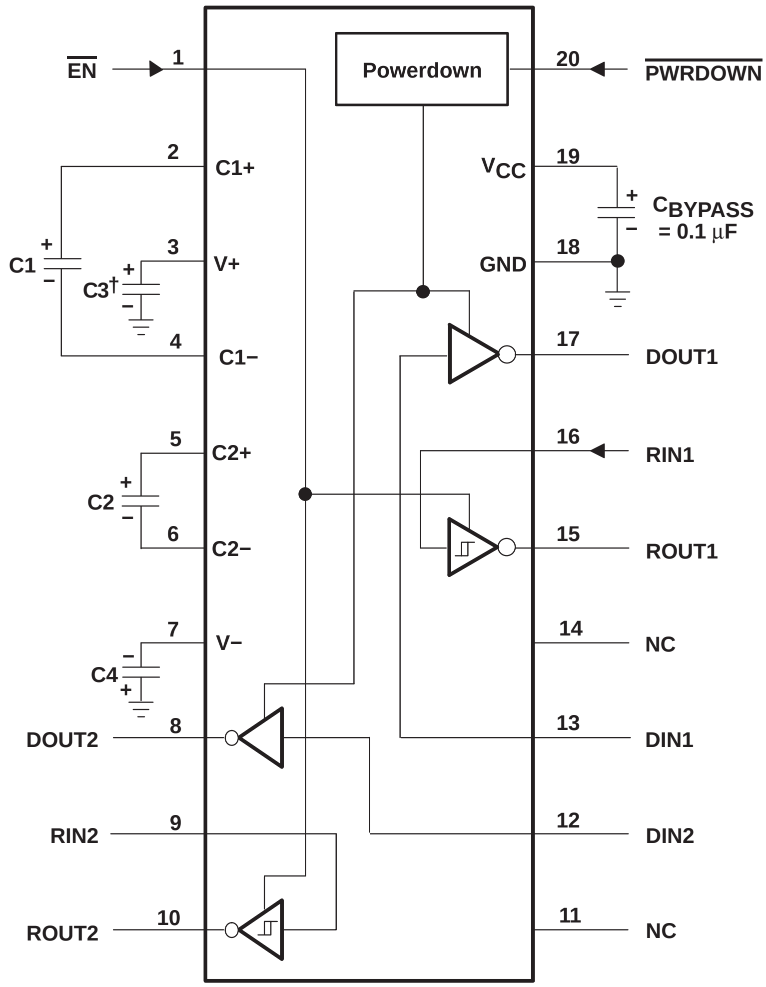


VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq$ 10 ns, $t_f \leq$ 10 ns.

Figure 4. Receiver Enable and Disable Times

APPLICATION INFORMATION



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. NC − No internal connection

C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

Figure 5. Typical Operating Circuit and Capacitor Values

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
MAX3222CDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDBE4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDBRE4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDWE4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDWRE4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPWE4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPWRE4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222CPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDBE4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDBRE4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
MAX3222IDWE4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDWRE4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPWE4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPWRE4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
MAX3222IPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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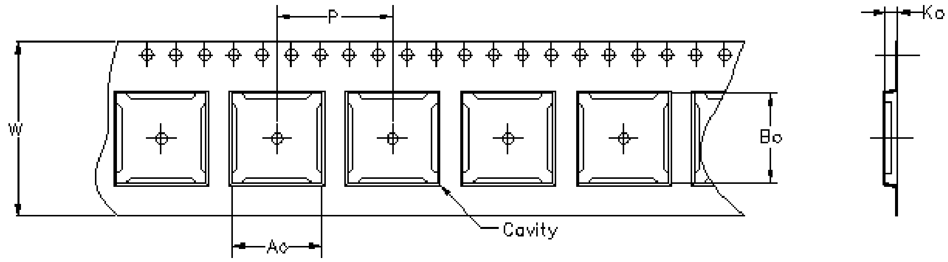
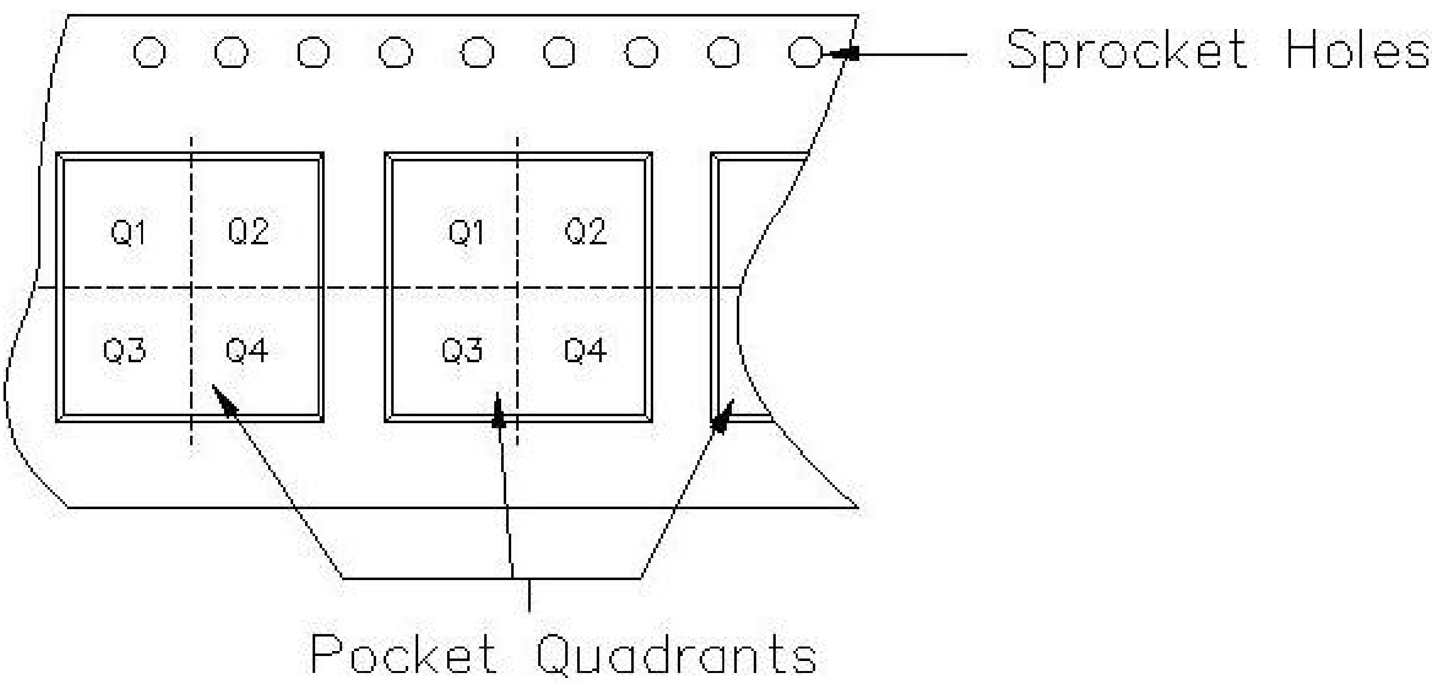


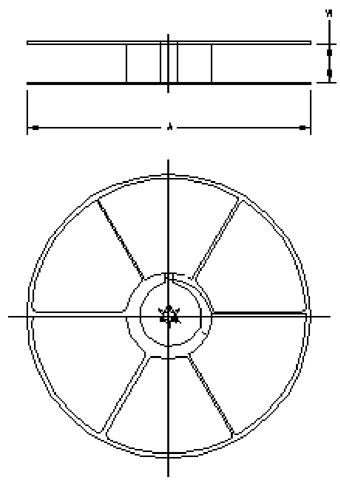
Carrier tape design is defined largely by the component lentgh, width, and thickness.

Ao = Dimension designed to accommodate the component width.
Bo = Dimension designed to accommodate the component length.
Ko = Dimension designed to accommodate the component thickness.
W = Overall width of the carrier tape.
P = Pitch between successive cavity centers.



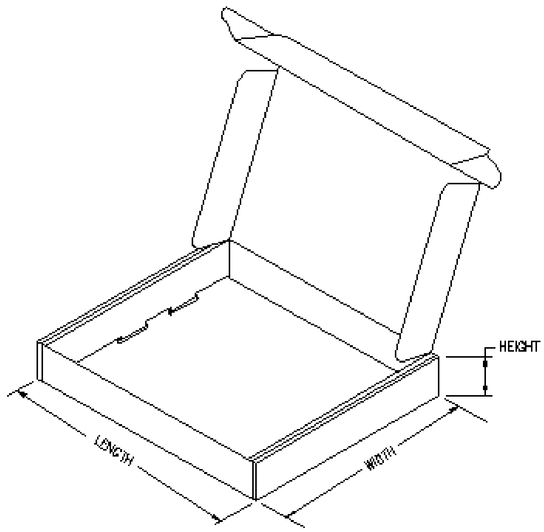
TAPE AND REEL INFORMATION

Device	Package	Pins	Site	Reel Diameter (mm)	Reel Width (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3222CDBR	DB	20	MLA	330	16	8.2	7.5	2.5	12	16	Q1
MAX3222CDWR	DW	20	MLA	330	24	10.8	13.0	2.7	12	24	Q1
MAX3222CPWR	PW	20	MLA	330	16	6.95	7.1	1.6	8	16	Q1
MAX3222IDBR	DB	20	MLA	330	16	8.2	7.5	2.5	12	16	Q1
MAX3222IDWR	DW	20	MLA	330	24	10.8	13.0	2.7	12	24	Q1
MAX3222IPWR	PW	20	MLA	330	16	6.95	7.1	1.6	8	16	Q1

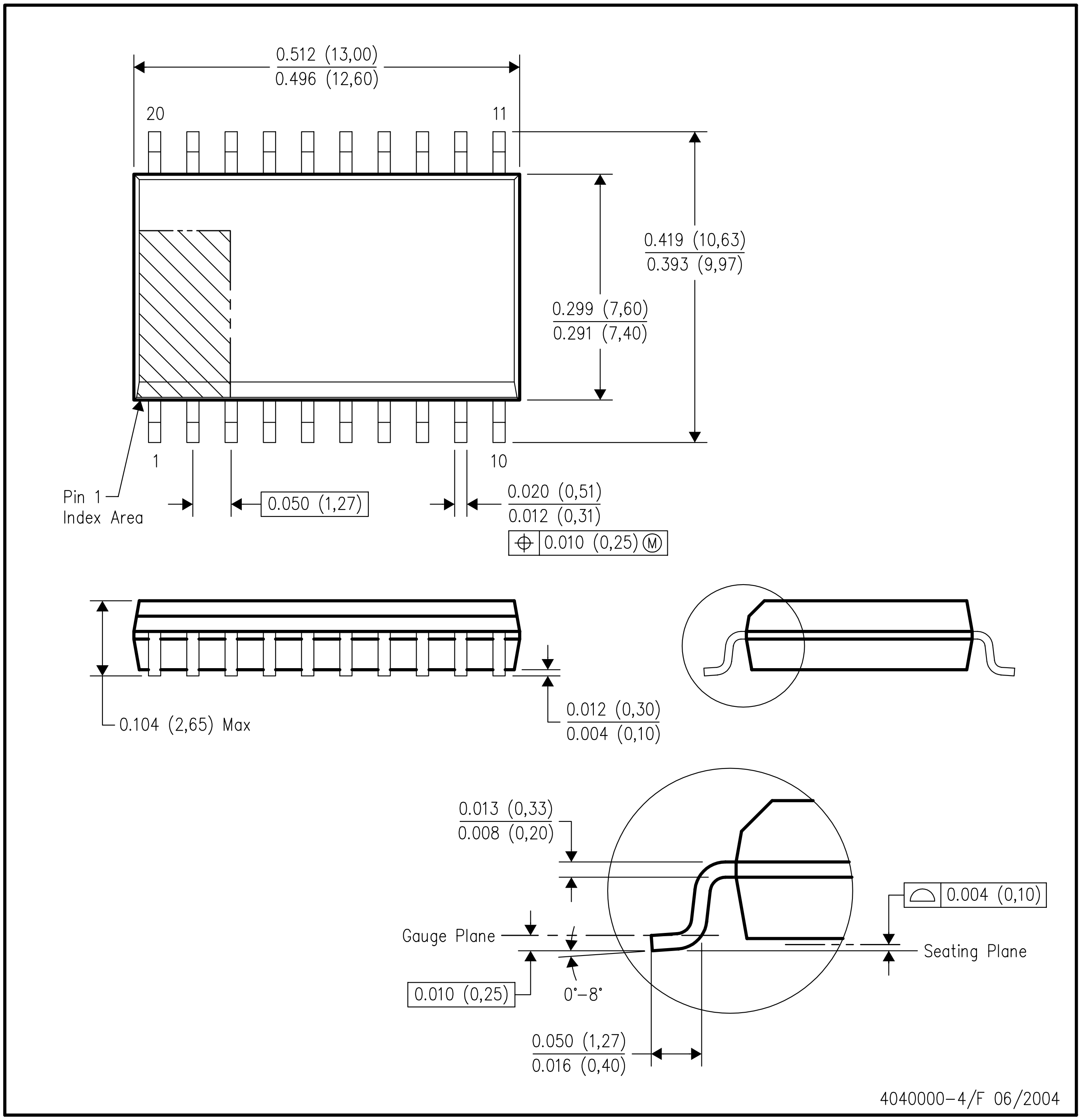


TAPE AND REEL BOX INFORMATION

Device	Package	Pins	Site	Length (mm)	Width (mm)	Height (mm)
MAX3222CDBR	DB	20	MLA	346.0	346.0	33.0
MAX3222CDWR	DW	20	MLA	333.2	333.2	31.75
MAX3222CPWR	PW	20	MLA	346.0	346.0	33.0
MAX3222IDBR	DB	20	MLA	346.0	346.0	33.0
MAX3222IDWR	DW	20	MLA	333.2	333.2	31.75
MAX3222IPWR	PW	20	MLA	346.0	346.0	33.0


HEIGHT
LENGTH
WIDTH

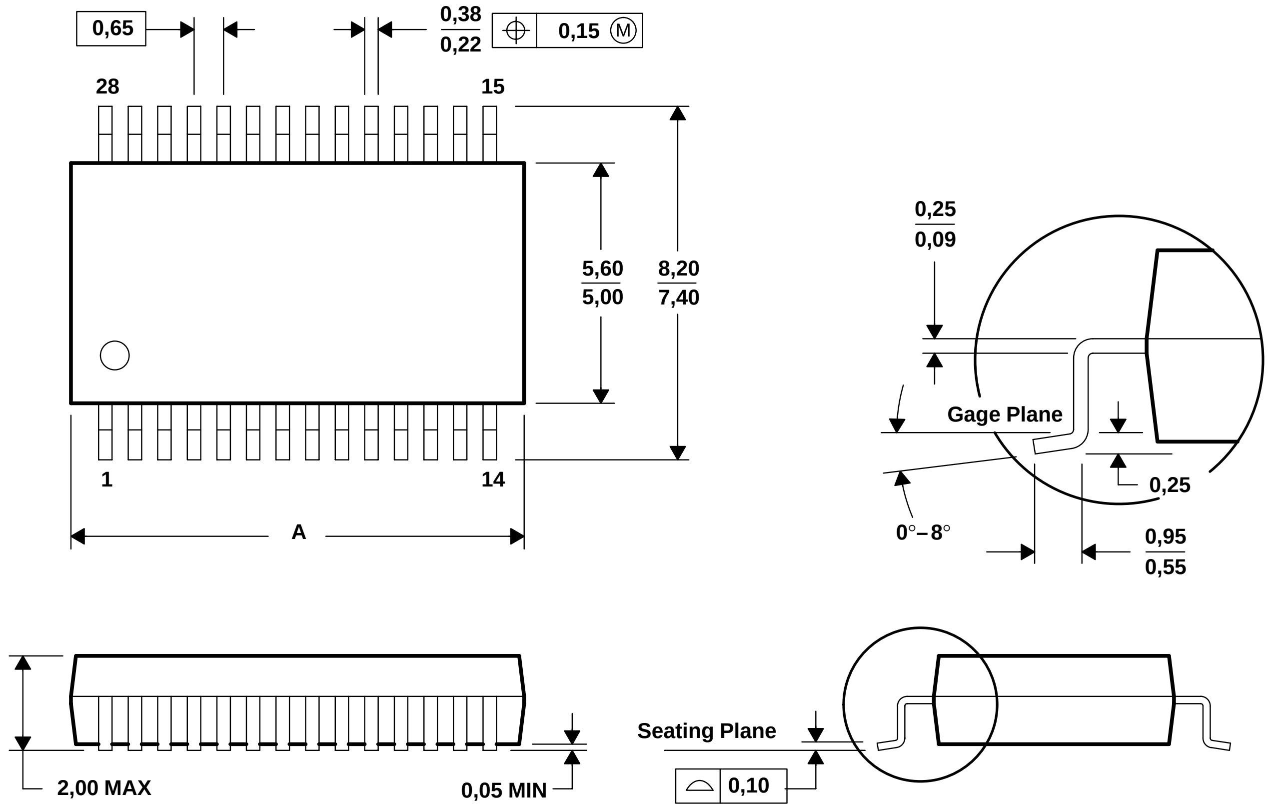
DW (R–PDSO–G20) PLASTIC SMALL–OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AC.

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



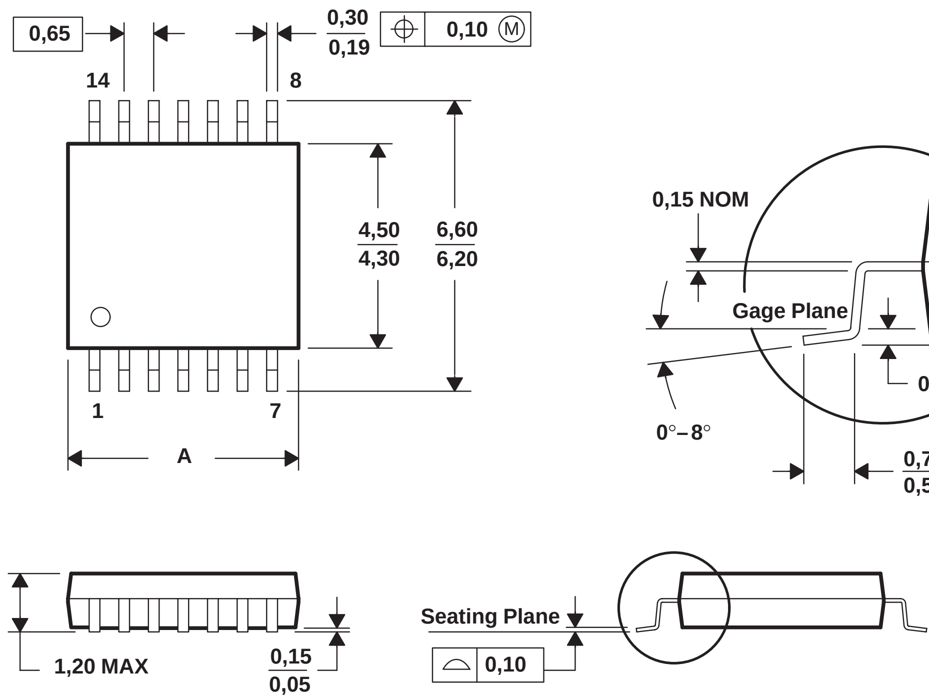
PINS ** / DIM	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

PW (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PINS SHOWN



PINS ** / DIM	8	14	16	20	24	28
A MAX	3,10	5,10	5,10	6,60	7,90	9,80
A MIN	2,90	4,90	4,90	6,40	7,70	9,60

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NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153

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